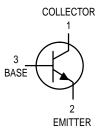
# **RF Transistor**

# **NPN Silicon**



# **BF224**



#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	VCEO	30	Vdc	
Collector-Base Voltage	Vсво	45	Vdc	
Emitter-Base Voltage	VEBO	4.0	Vdc	
Collector Current — Continuous	lC	50	mAdc	
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C	
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.0 8.0		
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V(BR)CEO	30	_	_	Vdc
Collector-Base Breakdown Voltage (IC = 100 µAdc, IE = 0)	V(BR)CBO	45	_	_	Vdc
Emitter-Base Breakdown Voltage (IE = 100 μAdc, IC = 0)	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 20 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	_	100	nAdc
Emitter Cutoff Current (VEB = 3.0 Vdc, IC = 0)	I <sub>EBO</sub>	_	_	100	nAdc

### **BF224**

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS					
DC Current Gain (IC = 7.0 mAdc, VCE = 10 Vdc)	hFE	30		_	_
Base–Emitter On Voltage ( $I_C = 7.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ )	V <sub>BE(on)</sub>	_	0.77	0.9	mVdc
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc)	VCE(sat)	_	_	0.15	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current Gain — Bandwidth Product ( $I_C = 1.5 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 100 \text{ MHz}$ ) ( $I_C = 7.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 100 \text{ MHz}$ )	fΤ	300 —	600 850	_ _	MHz
Common Emitter Feedback Capacitance (V <sub>CE</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>re</sub>	_	0.28	_	pF
Noise Figure (I <sub>C</sub> = 1.0 mAdc, $V_{CE}$ = 10 Vdc, $R_S$ = 50 $\Omega$ , f = 100 MHz) (I <sub>C</sub> = 1.0 mAdc, $V_{CE}$ = 10 Vdc, $R_S$ = 50 $\Omega$ , f = 200 MHz)	N <sub>f</sub>	_ _	2.5 3.5	_ _	dB

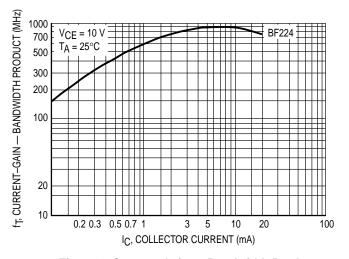


Figure 1. Current-Gain — Bandwidth Product

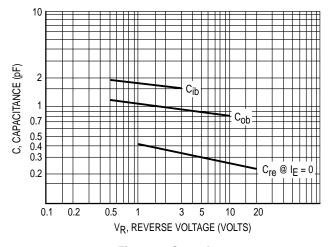


Figure 2. Capacitances

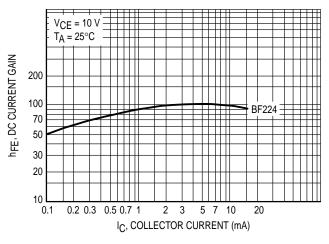


Figure 3. DC Current Gain

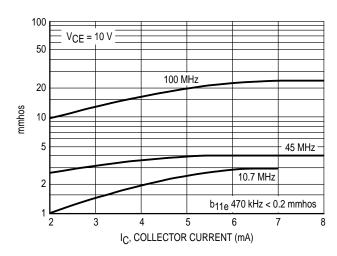


Figure 4. b11e

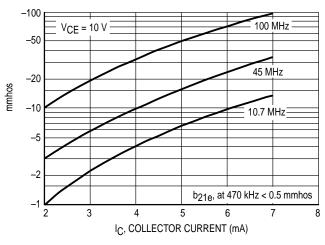


Figure 5. b21e

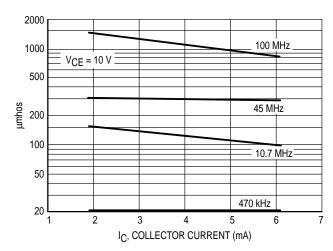
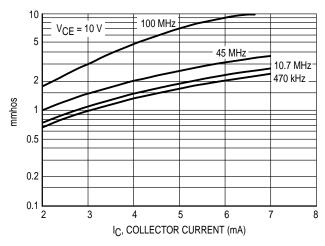


Figure 6. b22e (boe)

### **BF224**



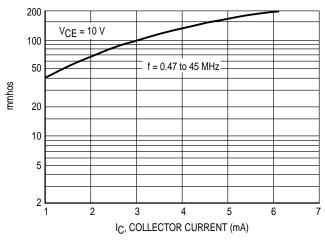


Figure 7. g11e (gie)

Figure 8. g21e (Yfe)

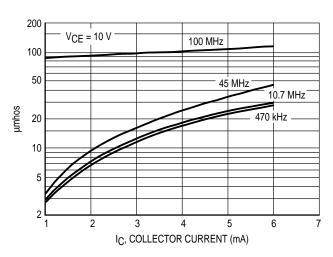
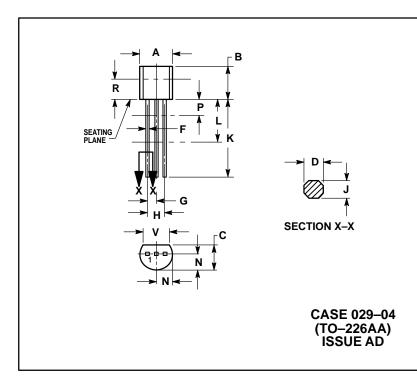


Figure 9. g22e (goe)

#### **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3 43	

STYLE 21:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

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